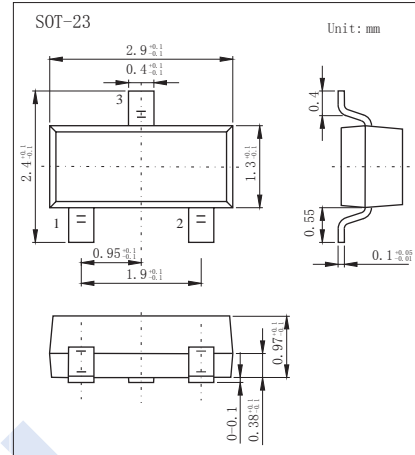
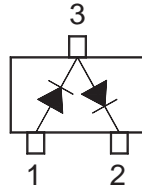


Switching Diodes

BAV99 (KAV99)

■ Features

- Fast Switching Speed
- For General Purpose Switching Applications.
- High Conductance

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Continuous Reverse Voltage	V_R	75	
Forward Current (Double Diode Loaded)	I_F	125	mA
Forward Current (Single Diode Loaded)		215	
Repetitive Peak Forward Current	I_{FRM}	450	A
Non-repetitive Peak Forward Surge Current	$t=1\text{s}$	0.5	
	$t=1\text{ms}$	1	
	$t=1\mu\text{s}$	1.5	
Power Dissipation	P_d	350	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-65 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100\ \mu\text{A}$	100			V
Forward voltage	V_F	$I_F = 1\ \text{mA}$			0.715	
		$I_F = 10\ \text{mA}$			0.855	
		$I_F = 50\ \text{mA}$			1	
		$I_F = 150\ \text{mA}$			1.25	
Reverse voltage leakage current	I_R	$V_R = 25\ \text{V}$			30	nA
		$V_R = 75\ \text{V}$			1	uA
		$V_R = 25\ \text{V}, T_J = 150^\circ\text{C}$			30	
		$V_R = 75\ \text{V}, T_J = 150^\circ\text{C}$			50	
Junction capacitance	C_j	$V_R = 0\ \text{V}, f = 1\ \text{MHz}$			1.5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10\ \text{mA}, I_R = 1\ \text{mA}, R_L = 100\ \Omega$			4	ns

■ Marking

Marking	A7*
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Switching Diodes

BAV99 (KAV99)

■ Typical Characteristics

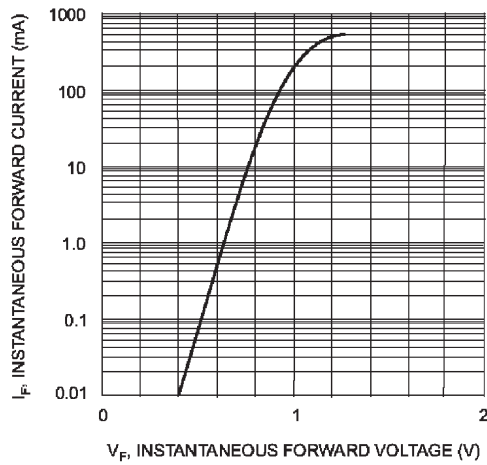


Fig. 1 Forward Characteristics

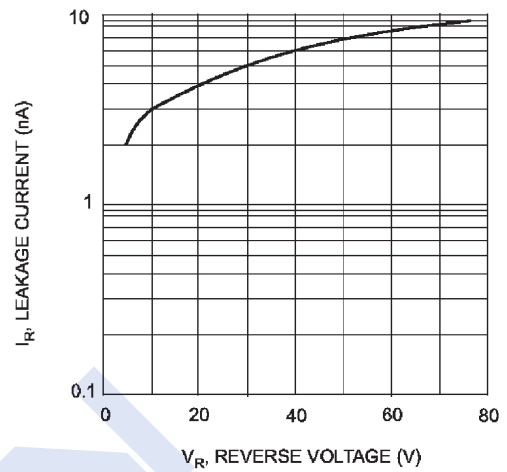


Fig. 2 Typical Leakage Current vs Reverse Voltage

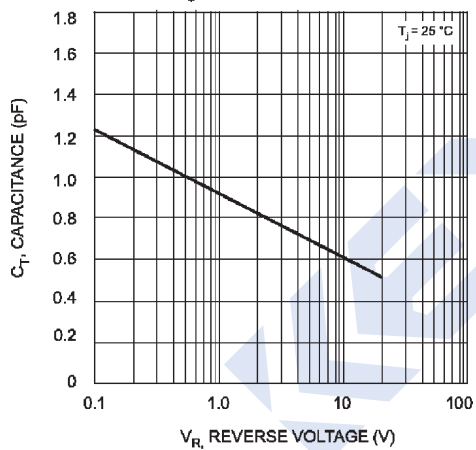


Fig. 3 Typical Total Capacitance vs Reverse Voltage